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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Compl to If Known	
				Application Number	10/077,784
				Filing Date	February 20, 2002
				First Named Inventor	Terry L. Gilton
				Art Unit	2818
				Examiner Name	Not Yet Assigned PHAN
Sheet	1	of	1	Attorney Docket Number	M4065.0482/P482

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
TP	A	5,883,827	3/16/1999	Morgan	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
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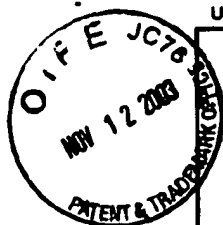
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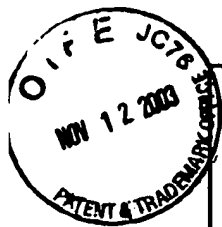
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	AL				
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TP	BA	WO 02/21542	03/14/2002	Kozicki et al.		
TP	BB	WO 00/48196	08/17/2000	Kozicki et al.		
TP	BC	WO 97/48032	12/18/1997	Kozicki et al.		
TP	BD	WO 99/28914	06/10/1999	Kozicki et al.		

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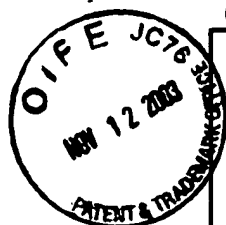
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
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PTO/SB/08B (10-01)

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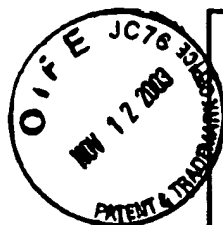
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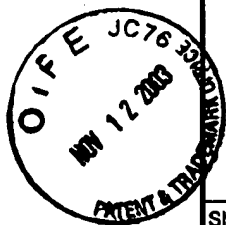
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				Filing Date	February 20, 2002
				First Named Inventor	Terry L. Gilton
				Group Art Unit	2818
				Examiner Name	Not Yet Assigned PHAN
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Group Art Unit	2818
Examiner Name	Not Yet Assigned PHAN
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Examiner Signature	Trong Phan	Date Considered	1/22/04
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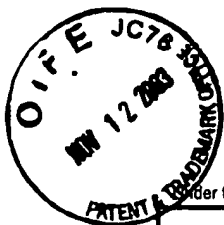
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				First Named Inventor	Gilton, et al.
				Art Unit	2818
				Examiner Name	T. Phan
Sheet	1	of	4	Attorney Docket Number	M4065.0482/P482

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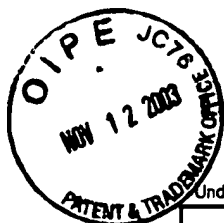
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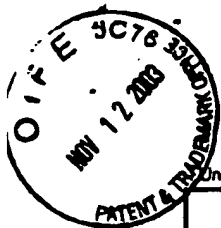
Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	10/077,784
				Filing Date	February 20, 2002
				First Named Inventor	Gilton, et al.
				Art Unit	2818
				Examiner Name	T. Phan
Sheet	4	of	4	Attorney Docket Number	M4065.0482/P482

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials [*]	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
TP	CA	Axon Technologies Corporation, TECHNOLOGY DESCRIPTION: <i>Programmable Metalization Cell(PMC)</i> , pp. 1-6 (Pre-May 2000).	
	CB	Helbert et al., <i>Intralevel hybrid resist process with submicron capability</i> , SPIE Vol. 333 SUBMICRON LITHOGRAPHY, pp. 24-29 (1982).	
	CC	Hilt, DISSERTATION: <i>Materials characterization of Silver Chalcogenide Programmable Metalization</i>	
	CD	Hirose et al., <i>High Speed Memory Behavior and Reliability of an Amorphous As₂S₃ Film Doped Ag</i> , PHYS. STAT. SOL. (a) 61, pp. 87-90 (1980).	
	CE	Holmquist et al., <i>Reaction and Diffusion in Silver-Arsenic Chalcogenide Glass Systems</i> , 62 J. AMER. CERAM. SOC., No. 3-4, pp. 183-188 (March-April 1979).	
	CF	Huggett et al., <i>Development of silver sensitized germanium selenide photoresist by reactive sputter etching in SF₆</i> , 42 Appl. Phys. Lett., No. 7, pp. 592-594 (April 1983).	
	CG	Kawaguchi et al., <i>Mechanism of photosurface deposition</i> , 164-166 J. NON-CRYST. SOLIDS, pp. 1231-1234 (1993).	
	CH	Kolobov et al., <i>Photodoping of amorphous chalcogenides by metals</i> , Advances in Physics, 1991, Vol. 40, No. 5, pgs. 625-684.	
	CI	Kozicki et al., <i>Silver incorporation in thin films of selenium rich Ge-Se glasses</i> , International Congress on Glass, Volume 2, Extended Abstracts, July 2001, pgs. 8-9.	
	CJ	Michael N. Kozicki, 1. <i>Programmable Metalization Cell Technology Description</i> , February 18, 2000	
	CK	Michael N. Kozicki, Axon Technologies Corp. and Arizona State University, Presentation to Micron Technology, Inc., April 6, 2000	
	CL	Kozicki et al., <i>Applications of Programmable Resistance Changes In Metal-Doped Chalcogenides</i> , Electrochemical Society Proceedings, Volume 99-13, 1999, pgs. 298-309.	
	CM	Kozicki et al., <i>Nanoscale effects in devices based on chalcogenide solid solutions, Superlattices and Microstructures</i> , Vol. 27, No. 516, 2000, pgs. 485-488.	
	CN	Kozicki et al., <i>Nanoscale phase separation in Ag-Ge-Se glasses</i> , Microelectronic Engineering 63 (2002) pgs 155-159.	
	CO	McHardy et al., <i>The dissolution of metals in amorphous chalcogenides and the effects o electron and ultraviolet radiation</i> , 20 J. Phys. C.: Solid State Phys., pp. 4055-4075 (1987)f	
↓	CP	Owens et al., <i>Metal-Chalcogenide Photoresists for High Resolution Lithography and Sub-Micron Structures</i> , Nanostructure Physics and Fabrication, pp. 447-451 (M. Reed ed. 1989).	
TP	CQ	Shimizu et al., <i>The Photo-Erasable Memory Switching Effect of Ag Photo-Doped Chalcogenide Glasses</i> , 46 B. CHEM SOC. JAPAN, No. 12, pp. 3662-3365 (1973).	

Examiner Signature	Trong Phan	Date Considered	1/22/04
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				Art Unit	2818
				Examiner Name	Not Yet Assigned PHAN
Sheet	1	of	1	Attorney Docket Number	M4065.0482/P482

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.†	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code² (if known)			
TP	AA	6,469,364-B1	10-22-2002	Kozicki	
TP	AB	2002/0168820-A1	11-14-2002	Kozicki et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No.†	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T
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Examiner Signature	Trong Phan	Date Considered	1/22/04
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